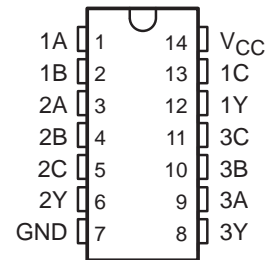


SN74ALVC10 TRIPLE 3-INPUT POSITIVE-NAND GATE

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- **EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (D), Thin Very Small-Outline (DGV), and Thin Shrink Small-Outline (PW) Packages**

**D, DGV, OR PW PACKAGE
(TOP VIEW)**



description

This triple 3-input positive-NAND gate is designed for 1.65-V to 3.6-V V_{CC} operation.

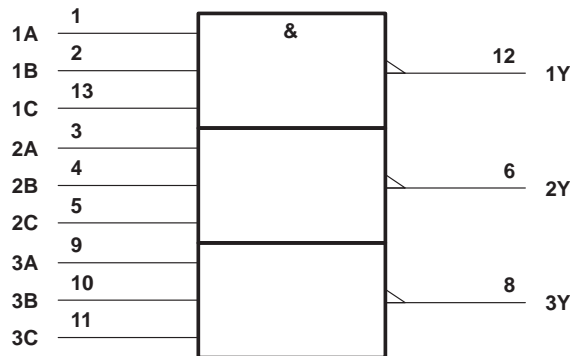
The SN74ALVC10 performs the Boolean function $Y = \overline{A \cdot B \cdot C}$ or $Y = \overline{A} + \overline{B} + \overline{C}$ in positive logic.

The SN74ALVC10 is characterized for operation from -40°C to 85°C.

**FUNCTION TABLE
(each gate)**

INPUTS			OUTPUT
A	B	C	Y
H	H	H	L
L	X	X	H
X	L	X	H
X	X	L	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

**TEXAS
INSTRUMENTS**

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SN74ALVC10

TRIPLE 3-INPUT POSITIVE-NAND GATE

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	MIN	TYP†	MAX	UNIT
V _{OH}	I _{OH} = -100 μA	1.65 V to 3.6 V	V _{CC} -0.2			V
	I _{OH} = -4 mA	1.65 V	1.2			
	I _{OH} = -6 mA	2.3 V	2			
	I _{OH} = -12 mA	2.3 V	1.7			
		2.7 V	2.2			
	I _{OH} = -24 mA	3 V	2.4			
V _{OL}	I _{OL} = 100 μA	1.65 V to 3.6 V			0.2	V
	I _{OL} = 4 mA	1.65 V			0.45	
	I _{OL} = 6 mA	2.3 V			0.4	
	I _{OL} = 12 mA	2.3 V			0.7	
		2.7 V			0.4	
	I _{OL} = 24 mA	3 V			0.55	
I _I	V _I = V _{CC} or GND	3.6 V			±5	μA
I _{CC}	V _I = V _{CC} or GND, I _O = 0	3.6 V			10	μA
ΔI _{CC}	One input at V _{CC} - 0.6 V, Other inputs at V _{CC} or GND	3 V to 3.6 V			750	μA
C _i	V _I = V _{CC} or GND	3.3 V		4		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 2.7 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A, B, or C	Y	1.1	4.8	1	3	3.3		1	3	ns

operating characteristics, T_A = 25°C

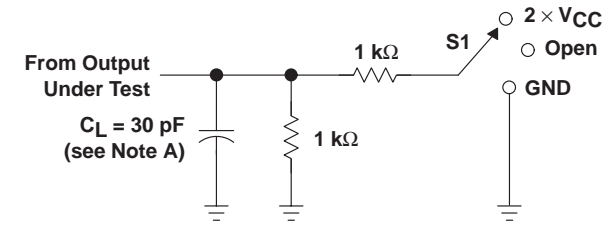
PARAMETER	TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	UNIT
		TYP	TYP	TYP	
C _{pd} Power dissipation capacitance per gate	C _L = 0, f = 10 MHz	23	24	26	pF



SN74ALVC10 TRIPLE 3-INPUT POSITIVE-NAND GATE

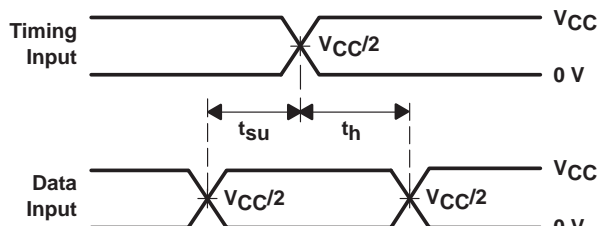
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PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.8\text{ V} \pm 0.15\text{ V}$

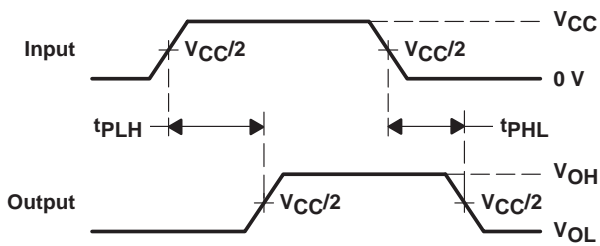


LOAD CIRCUIT

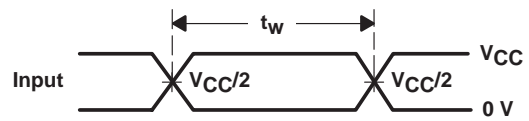
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	$2 \times V_{CC}$
t_{PHZ}/t_{PZH}	Open



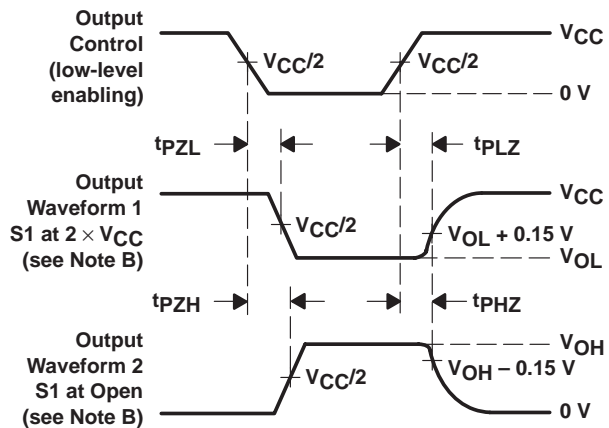
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



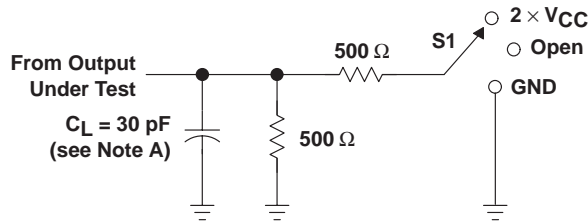
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_O = 50\ \Omega$, $t_r \leq 2\text{ ns}$, $t_f \leq 2\text{ ns}$.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 1. Load Circuit and Voltage Waveforms

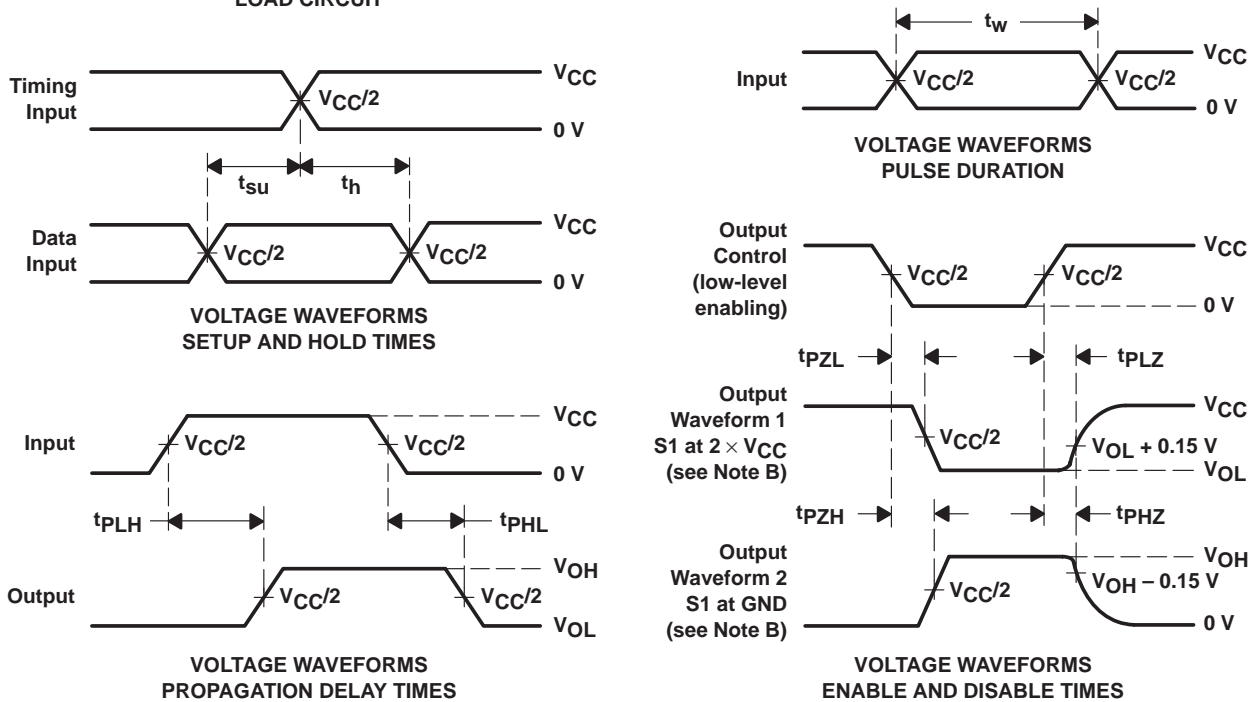
PARAMETER MEASUREMENT INFORMATION

$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$



LOAD CIRCUIT

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 $\times V_{CC}$
t_{PHZ}/t_{PZH}	GND



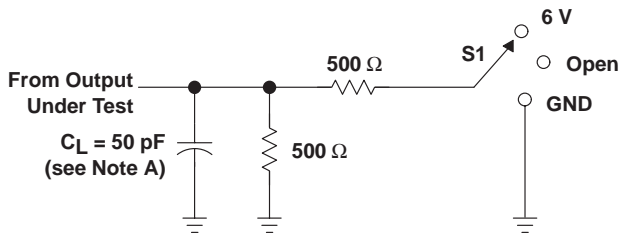
- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r \leq 2 \text{ ns}$, $t_f \leq 2 \text{ ns}$.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 2. Load Circuit and Voltage Waveforms

SN74ALVC10 TRIPLE 3-INPUT POSITIVE-NAND GATE

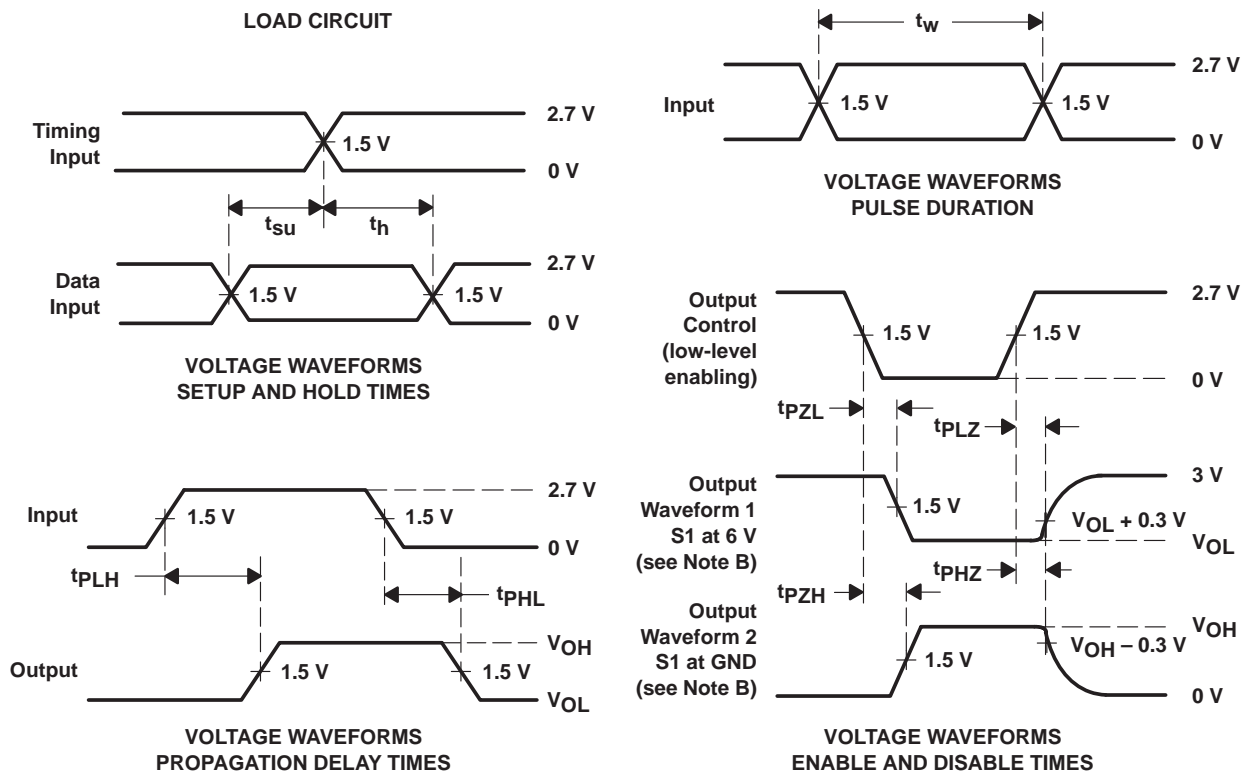
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PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.7\text{ V AND } 3.3\text{ V} \pm 0.3\text{ V}$



LOAD CIRCUIT

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



- NOTES: A. C_L includes probe and jig capacitance.
 B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_O = 50\ \Omega$, $t_r \leq 2.5\text{ ns}$, $t_f \leq 2.5\text{ ns}$.
 D. The outputs are measured one at a time with one transition per measurement.
 E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 F. t_{PZL} and t_{PZH} are the same as t_{en} .
 G. t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 3. Load Circuit and Voltage Waveforms

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